



TO-92 Plastic-Encapsulate Transistors

2SC2001 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.6 W ($T_{amb}=25^{\circ}C$)

Collector current

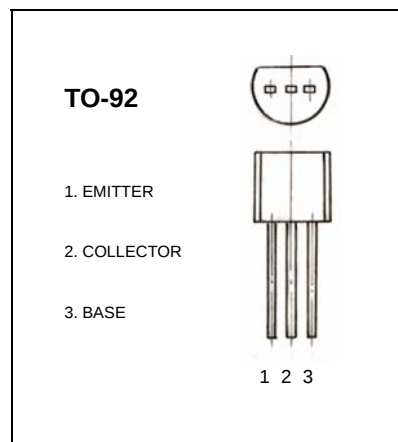
I_{CM} : 0.7 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	90	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=700mA, I_B=70mA$		0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=700mA, I_B=70mA$		1.2	V
Transition frequency	f_T	$V_{CE}=6V, I_C=10mA$ $f=30MHz$	50		MHz

CLASSIFICATION OF h_{FE}

Rank	M	L	K
Range	90-180	135-270	200-400